

## N-P-N SMALL-SIGNAL DARLINGTON TRANSISTORS

N-P-N small-signal darlington transistors in a microminiature SMD package (SOT-23).  
Designed primarily for preamplifier input applications requiring high input impedance.  
P-N-P complement is the PMBTA63/64.

### QUICK REFERENCE DATA

Collector-emitter voltage $V_{BE} = 0$		$V_{CES}$	max.	30 V
Collector current (d.c.)		$I_C$	max.	300 mA
Total power dissipation up to $T_{amb} = 25\text{ }^\circ\text{C}$		$P_{tot}$	max.	250 mW
Junction temperature		$T_j$	max.	150 $^\circ\text{C}$
D.C. current gain $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	PMBTA13	$h_{FE}$	min.	5000
	PMBTA14	$h_{FE}$	min.	10 000
Transition frequency at $f = 100\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$		$f_T$	min.	125 MHz

### MECHANICAL DATA

Dimensions in mm

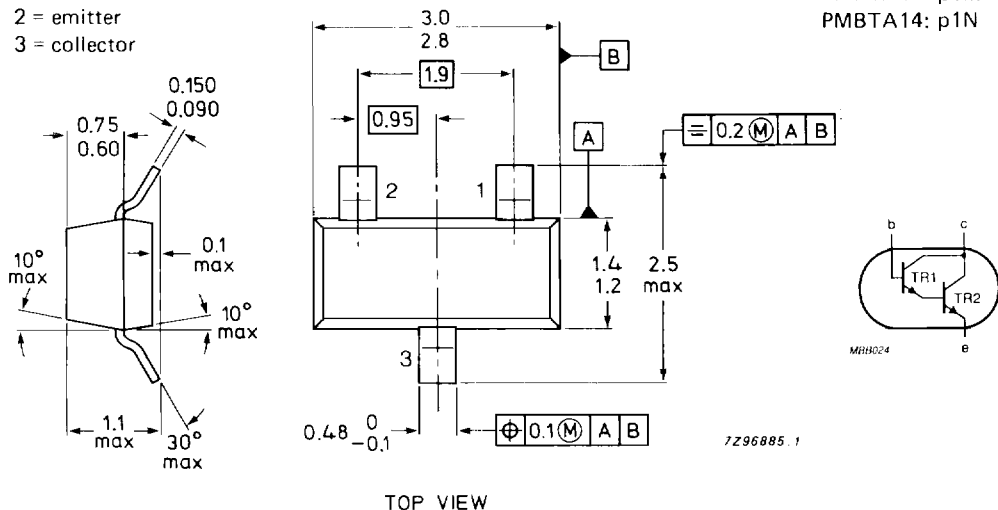
Fig. 1 SOT-23.

#### Pinning:

- 1 = base
- 2 = emitter
- 3 = collector

#### Marking code

PMBTA13: p1M  
PMBTA14: p1N



**RATINGS**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$V_{CBO}$	max.	30 V
Collector-emitter voltage $V_{BE} = 0$	$V_{CES}$	max.	30 V
Emitter-base voltage (open collector)	$V_{EBO}$	max.	10 V
Collector current (d.c.)	$I_C$	max.	300 mA
Total power dissipation up to $T_{amb} = 25\text{ }^\circ\text{C}$ *	$P_{tot}$	max.	250 mW
Storage temperature	$T_{stg}$		-65 to +150 $^\circ\text{C}$
Junction temperature	$T_j$	max.	150 $^\circ\text{C}$

**THERMAL RESISTANCE**

From junction to ambient*	$R_{th\ j-a}$		500 K/W
---------------------------	---------------	--	---------

**CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified

Collector-emitter breakdown voltage $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CES}$	min.	30 V
Emitter-base cut-off current $V_{BE} = 10\text{ V}$	$I_{EBO}$	max.	0,1 $\mu\text{A}$
Collector-base cut-off current $V_{CB} = 30\text{ V}$	$I_{CBO}$	max.	0,1 $\mu\text{A}$
D.C. current gain $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	PMBTA13 PMBTA14	$h_{FE}$	min. 5000 min. 10 000
$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$	PMBTA13 PMBTA14	$h_{FE}$	min. 10 000 min. 20 000
Collector-emitter saturation voltage $I_C = 100\text{ mA}; I_B = 0,1\text{ mA}$	$V_{CEsat}$	max.	1,5 V
Base-emitter ON-voltage $I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$	$V_{BE(on)}$	max.	2,0 V
Transition frequency at $f = 100\text{ MHz}$ $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	$f_T$	min.	125 MHz

\* Mounted on an FR4 printed-circuit board 8 mm x 10 mm x 0.7 mm.